

Features

- Two 2SA1037AK Chips in a Package
- Mounting Possible with SOT-363 Automatic Mounting Machines
- Transistor Elements are Independent, Eliminating Interference
- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

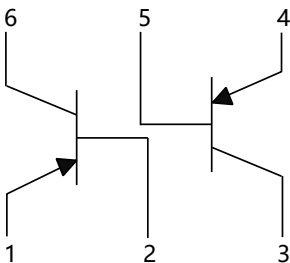
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 833°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Continuous Collector Current	I_C	-150	mA
Power Dissipation	P_D	150	mW

Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

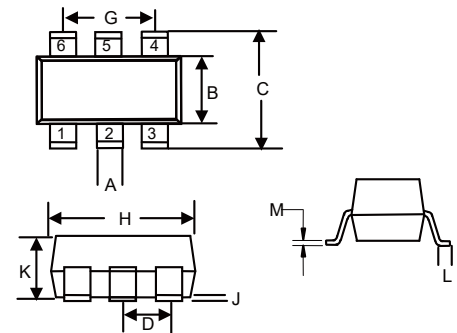
Marking: T1

Internal Structure



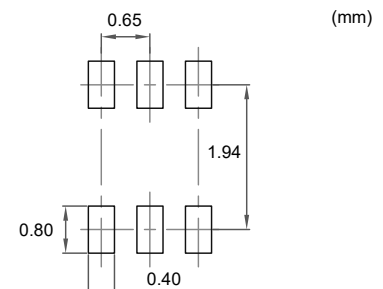
Dual PNP Transistors

SOT-363



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	0.006	0.014	0.15	0.35	
B	0.045	0.053	1.15	1.35	
C	0.079	0.096	2.00	2.45	
D	0.026		0.65		TYP.
G	0.047	0.055	1.20	1.40	
H	0.071	0.087	1.80	2.20	
J	-----	0.004	-----	0.10	
K	0.031	0.043	0.80	1.10	
L	0.010	0.018	0.26	0.46	
M	0.003	0.006	0.08	0.15	

Suggested Solder Pad Layout



Electrical Characteristics @ $T_A=25^\circ\text{C}$ Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60			V	$I_C=-50\mu\text{A}$, $I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-50			V	$I_C=-1\text{mA}$, $I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6			V	$I_E=-50\mu\text{A}$, $I_C=0$
Collector Cutoff Current	I_{CBO}			-0.1	μA	$V_{CB}=-60\text{V}$, $I_E=0$
Emitter Cutoff Current	I_{EBO}			-0.1	μA	$V_{EB}=-6\text{V}$, $I_C=0$
DC Current Gain	h_{FE}	120		560		$V_{CE}=-6\text{V}$, $I_C=-1\text{mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C=-50\text{mA}$, $I_B=-5\text{mA}$
Transition Frequency	f_T		140		MHz	$V_{CE}=-12\text{V}$, $I_E=2\text{mA}$, $f=100\text{MHz}$
Output Capacitance	C_{ob}			5	pF	$V_{CB}=-12\text{V}$, $I_E=0$, $f=1\text{MHz}$

Curve Characteristics

Fig. 1 - Static Characteristics

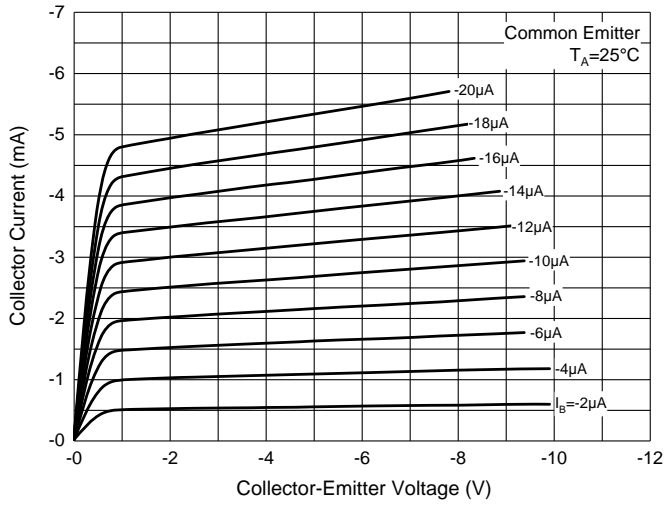


Fig. 2 - DC Current Gain Characteristics

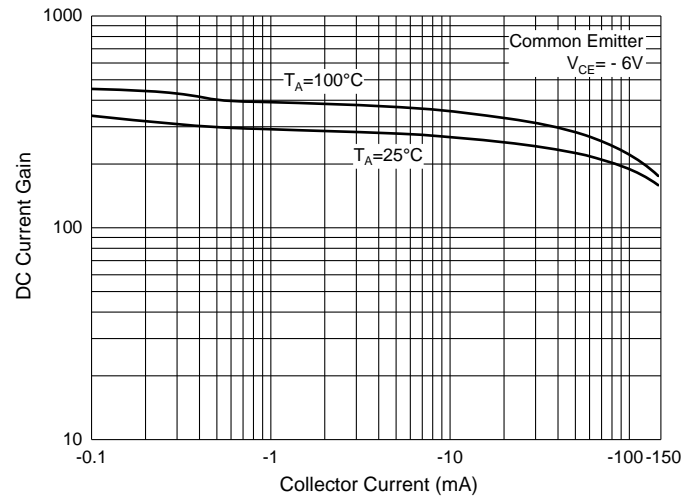


Fig. 3 - Base-Emitter Saturation Voltage Characteristics

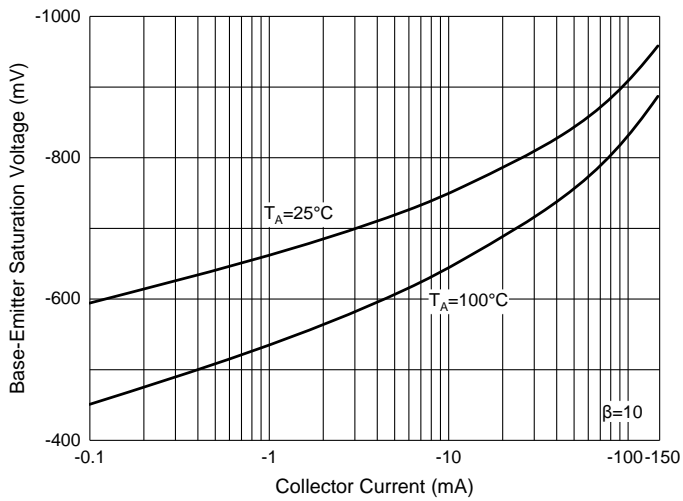


Fig. 4 - Collector-Emitter Saturation Voltage Characteristics

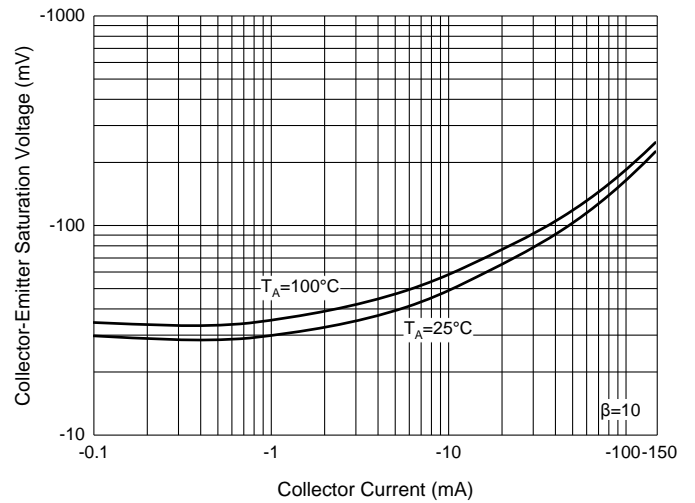


Fig. 5 - Base-Emitter Voltage Characteristics

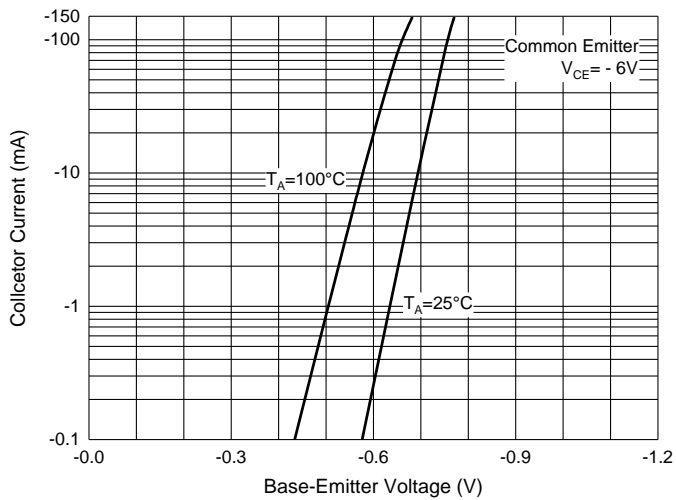


Fig. 6 - Collector Power Derating Curve

